

## ABSTRACT OF THE INVENTION

The present invention is a CMOS SRAM cell comprising two access devices, each access device comprised of a tri-gate transistor having a single fin; two pull-up devices, each pull-up device comprised of a tri-gate transistor having a single fin; and two pull-down devices, each pull-down device comprised of a tri-gate transistor having multiple fins. A method for manufacturing the CMOS SRAM cell, including the dual fin tri-gate transistor is also provided.